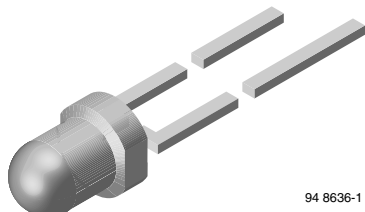


## Infrared Emitting Diode, RoHS Compliant, 950 nm, GaAs



94 8636-1

### DESCRIPTION

TSUS4300 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue tinted plastic package.

### FEATURES

- Package type: leaded
- Package form: T-1
- Dimensions (in mm):  $\varnothing 3$
- Peak wavelength:  $\lambda_p = 950$  nm
- High reliability
- Angle of half intensity:  $\varphi = \pm 16^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Package matches with detector TEFT4300
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### APPLICATIONS

- Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- Emitter in transmissive sensors
- Emitter in reflective sensors

### PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSUS4300	18	$\pm 16$	950	800

#### Note

Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSUS4300	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1

#### Note

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5$ , $t_p = 100 \mu s$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu s$	$I_{FSM}$	2	A
Power dissipation		$P_V$	170	mW
Junction temperature		$T_j$	100	$^\circ C$
Operating temperature range		$T_{amb}$	- 40 to + 85	$^\circ C$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	300	K/W

#### Note

$T_{amb} = 25 \text{ }^\circ C$ , unless otherwise specified

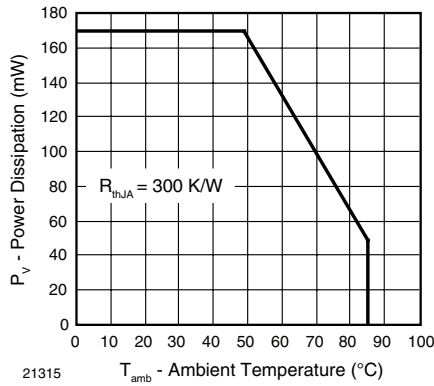


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

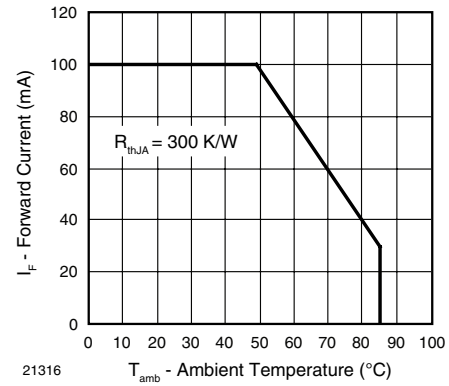


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	V <sub>F</sub>		1.3	1.7	V
	I <sub>F</sub> = 1.5 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>		2.2		V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA	TK <sub>V<sub>F</sub></sub>		- 1.3		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			100	μA
Breakdown voltage	I <sub>R</sub> = 100 μA	V <sub>(BR)</sub>	5	40		
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	C <sub>j</sub>		30		pF
Radiant intensity	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	I <sub>e</sub>	7	18	35	mW/sr
	I <sub>F</sub> = 1.5 A, t <sub>p</sub> = 100 μs	I <sub>e</sub>		160		mW/sr
Radiant power	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	φ <sub>e</sub>		20		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 20 mA	TKφ <sub>e</sub>		- 0.8		%/K
Angle of half intensity		φ		± 16		deg
Peak wavelength	I <sub>F</sub> = 100 mA	λ <sub>p</sub>		950		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		50		nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.2		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		800		ns
	I <sub>F</sub> = 1.5 A	t <sub>r</sub>		400		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		800		ns
	I <sub>F</sub> = 1.5 A	t <sub>f</sub>		400		ns
Virtual source diameter		d		2.1		mm

**Note**

 T<sub>amb</sub> = 25 °C, unless otherwise specified

**BASIC CHARACTERISTICS**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

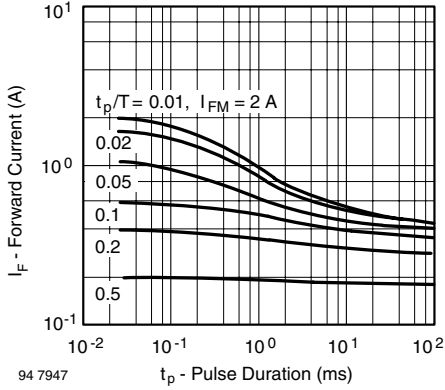


Fig. 3 - Pulse Forward Current vs. Pulse Duration

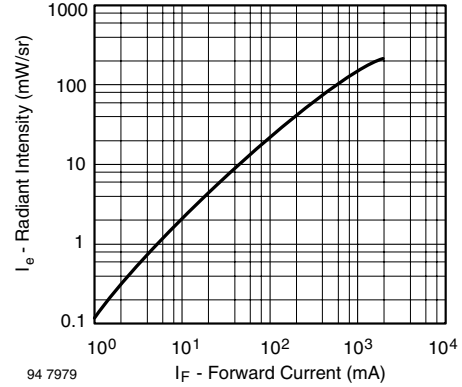


Fig. 6 - Radiant Intensity vs. Forward Current

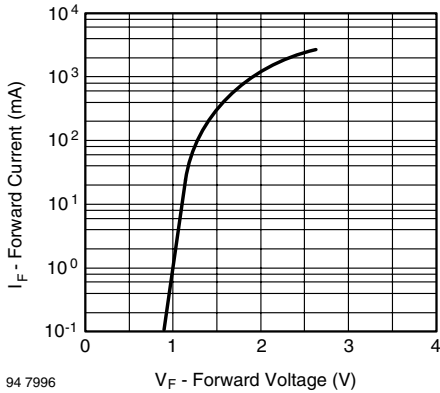


Fig. 4 - Forward Current vs. Forward Voltage

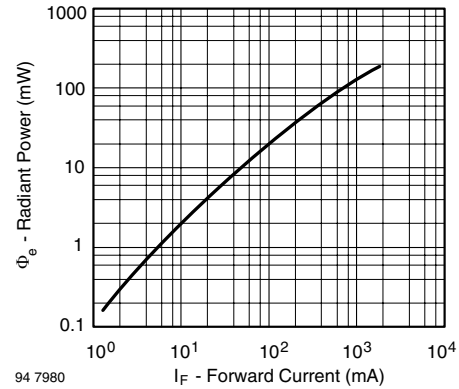


Fig. 7 - Radiant Power vs. Forward Current

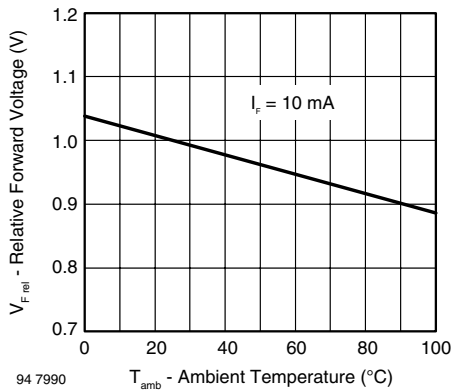


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

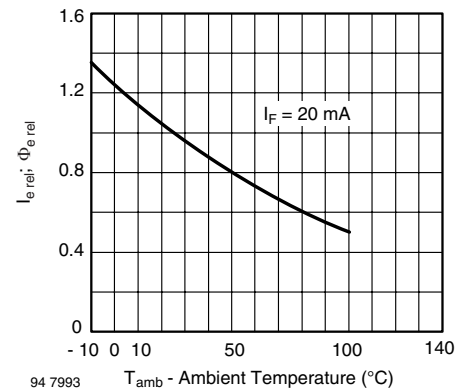


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

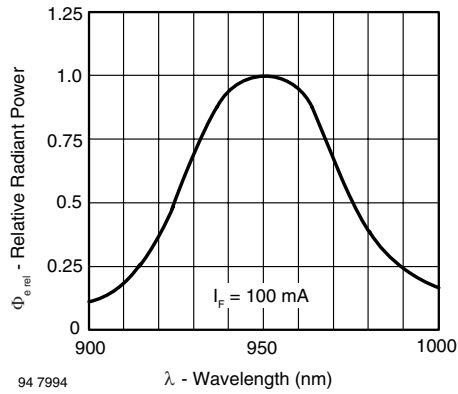


Fig. 9 - Relative Radiant Power vs. Wavelength

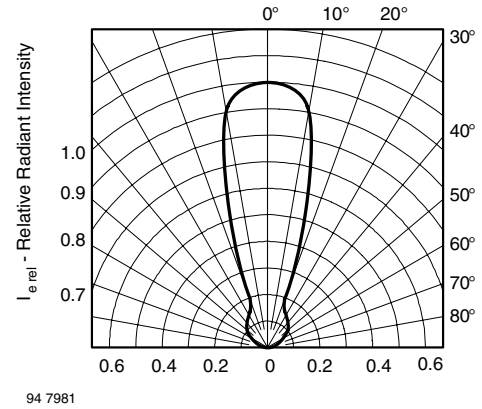
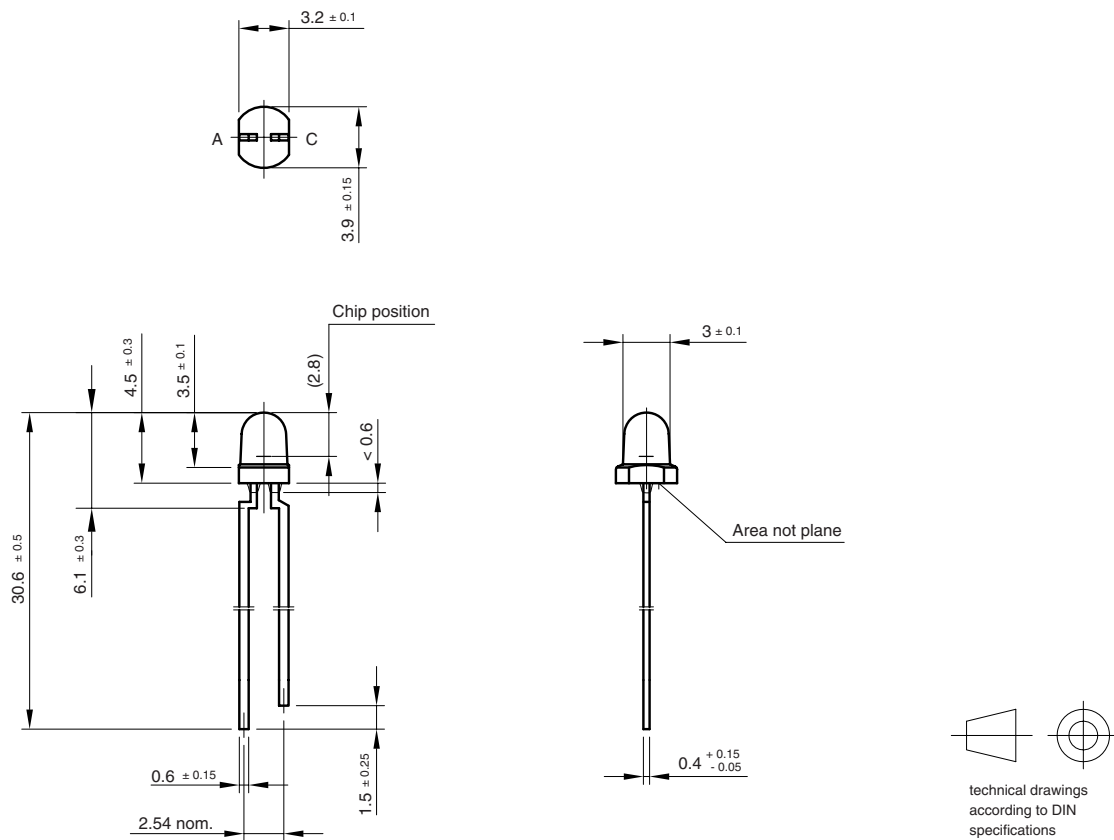


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

### PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.544-5269.02-4  
Issue: 3; 23.04.98  
96 12208

technical drawings  
according to DIN  
specifications



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